

P-Channel 20V (D-S) MOSFET

V_{DS}	$R_{DS(on)MAX}$	I_D
-20V	61 mΩ@-4.5V	-4.4A
	80 mΩ@-2.5V	-3.8A
	110 mΩ@-1.8V	-3.3A
	165 mΩ@-1.5V	-0.5A

Features

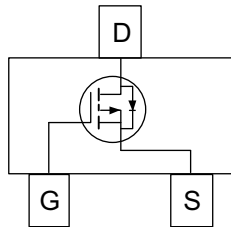
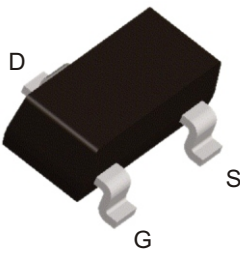
- Small package SOT23-3L
- Low Gate Charge
- RoHS Compliant

Applications

- Load Switch for Portable Devices

Pin Configuration

SOT23-3L



Packing Information

Device	Marking	Reel Size	Tape Width	Quantity
EC2377	13D .XXX	7"	8mm	3000pcs

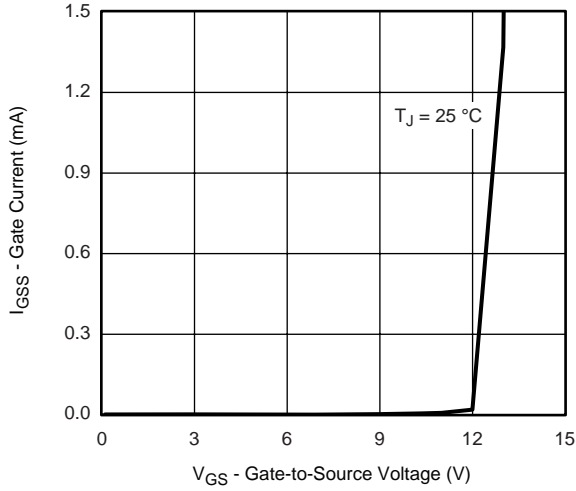
Absolute Maximum Ratings (T_J=25 °C Unless Otherwise Noted)

Symbol	Parameter	Value	Unit
P-MOSFET			
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±8	V
I_D	Continuous Drain Current	-4.4	A
I_{DM}	Pulse Drain Current	-20	A
P_D	Maximum Power Dissipation	1.8	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	180	°C/W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C
T_L	Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	260	°C
Thermal Resistance Ratings			
R_{thJA}	Maximum Junction-to-Ambient ^b	80	°C/W
	Maximum Junction-to-Ambient ^c	100	°C/W

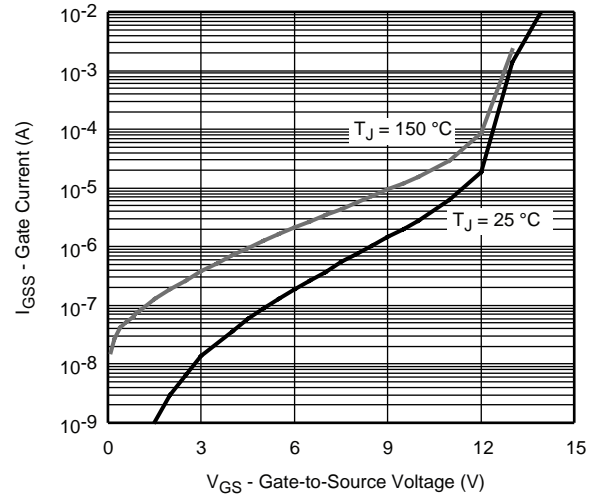
Electrical Characteristics (T_J = 25°C Unless Otherwise Specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -16V, V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±8V, V _{DS} = 0V			±6	μA
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.4		-1	V
Drain-source on-resistance(note1)	R _{DS(on)}	V _{GS} = -4.5V, I _D = -3.2A		50	61	mΩ
		V _{GS} = -2.5V, I _D = -2.8A		65	80	mΩ
		V _{GS} = -1.8V, I _D = -1.5A		90	110	mΩ
		V _{GS} = -1.5V, I _D = -0.5A		110	165	mΩ
Forward transconductance(note1)	g _{FS}	V _{DS} = -10V, I _D = -3.2A		12		S
Diode forward voltage(note1)	V _{SD}	I _S = -3A, V _{GS} = 0V		-0.8	-1.2	V
SWITCHING PARAMETERS (note 2)						
Turn-on delay time	t _{d(on)}	V _{GS} = -4.5V, V _{DD} = -10V, R _L = 2.3Ω, R _G = 1Ω, I _D = -4.3		0.2	0.3	μs
Turn-on rise time	t _r			1.00	1.50	μs
Turn-off delay time	t _{d(off)}			4.00	6.00	μs
Turn-off fall time	t _f			2.00	3.00	μs
Total Gate Charge	Q _g	V _{DS} = -10V, V _{GS} = -8V, I _D = -5.3A		14	21	nC
		V _{DS} = -10V, V _{GS} = -4.5V, I _D = -5.3A		7.6	12	nC
Gate-Source Charge	Q _{gs}	V _{DS} = -10V, V _{GS} = -4.5V, I _D = -5.3A		0.8		nC
Gate-Drain Charge	Q _{gd}			3.1		nC

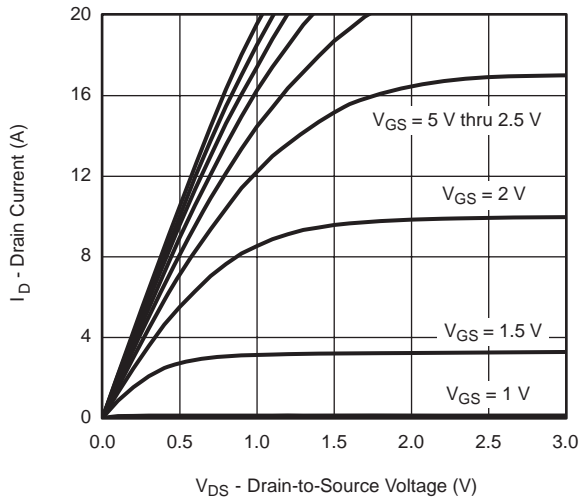
MOSFET TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)



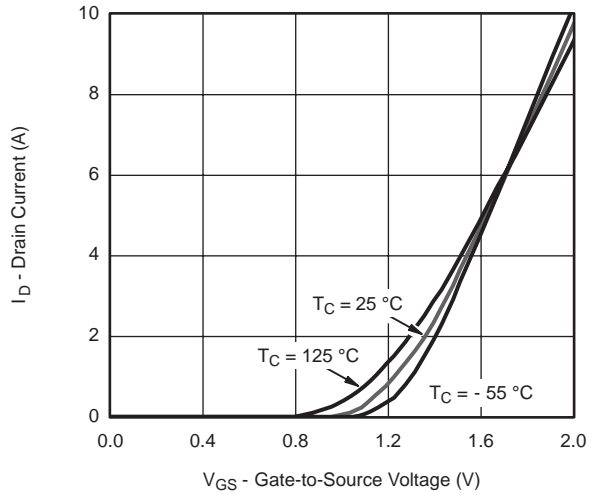
Gate Current vs. Gate-Source Voltage



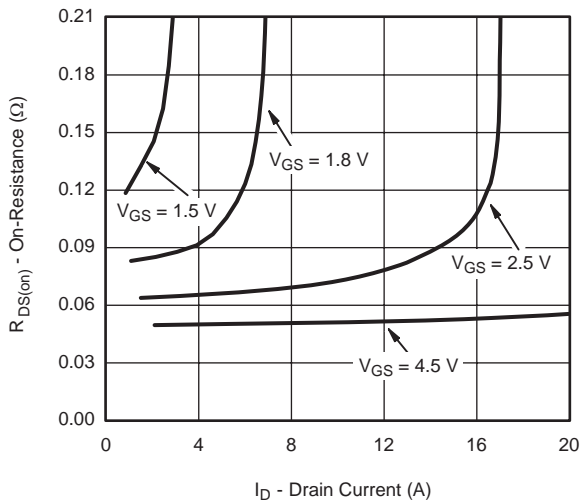
Gate Current vs. Gate-Source Voltage



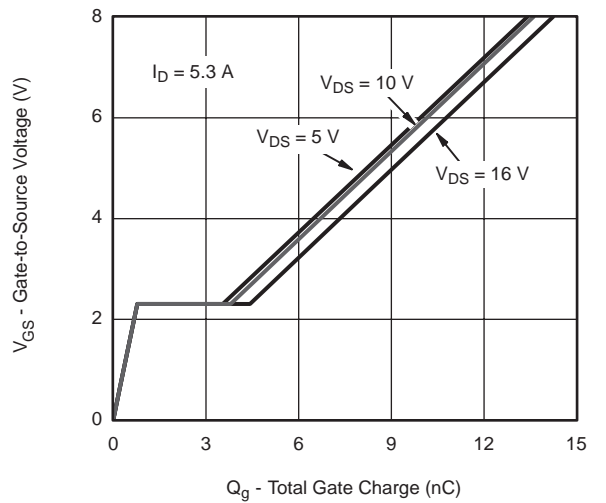
Output Characteristics



Transfer Characteristics

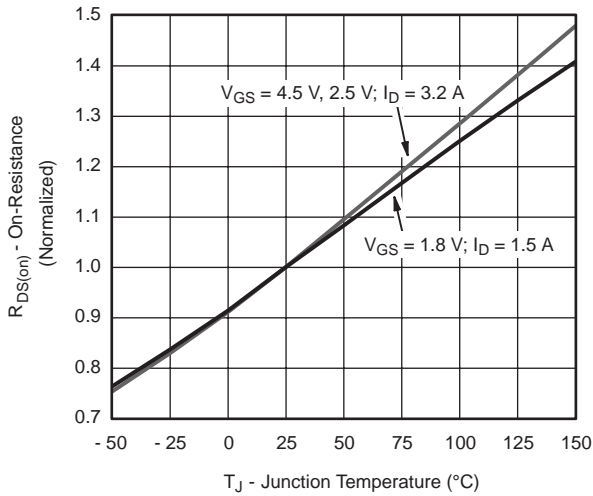


On-Resistance vs. Drain Current

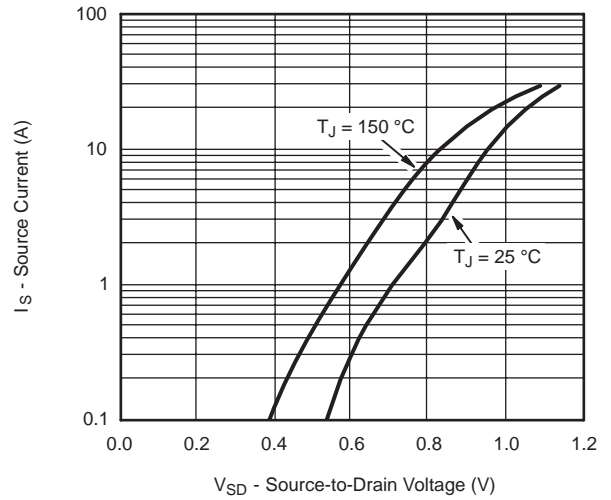


Gate Charge

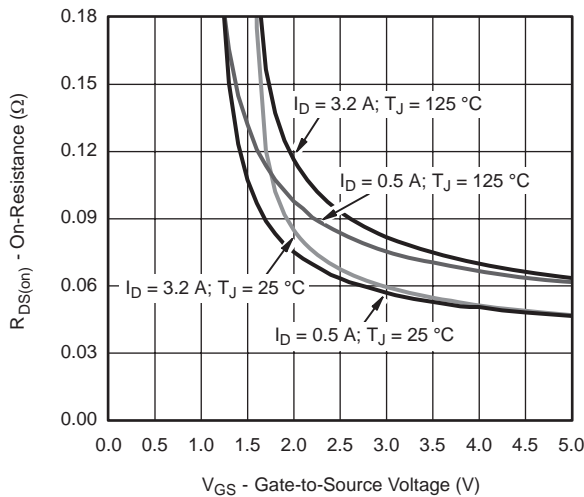
MOSFET TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)



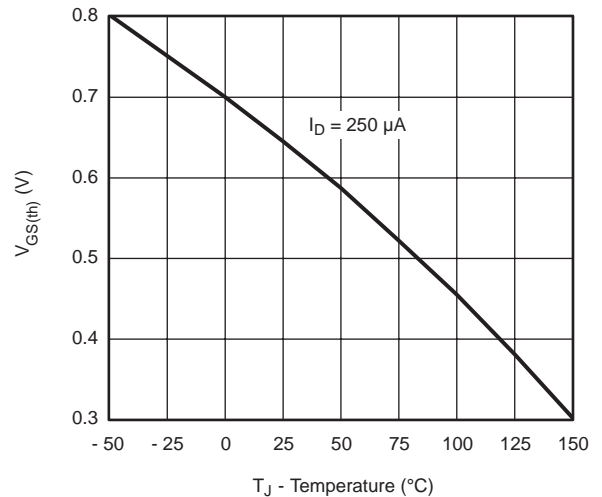
On-Resistance vs. Junction Temperature



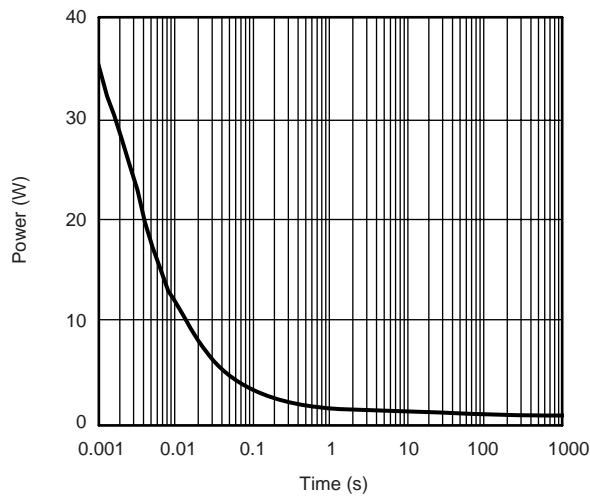
Source-Drain Diode Forward Voltage



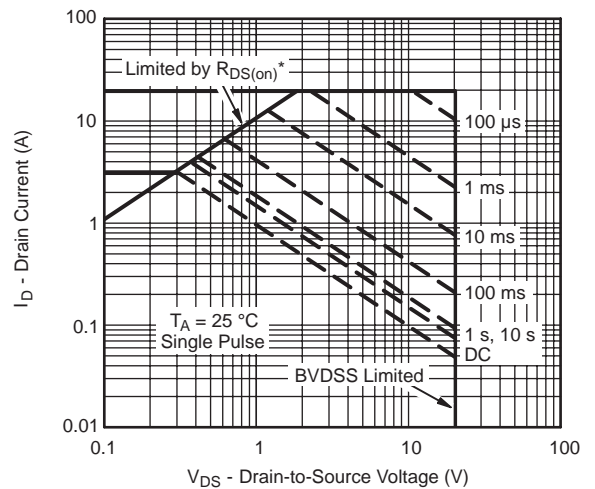
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



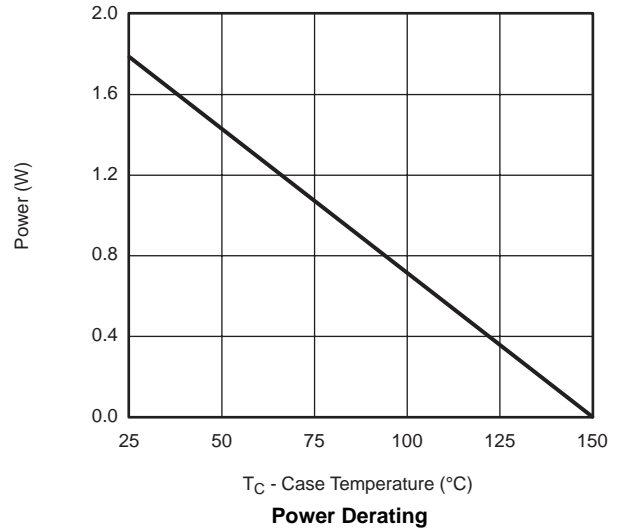
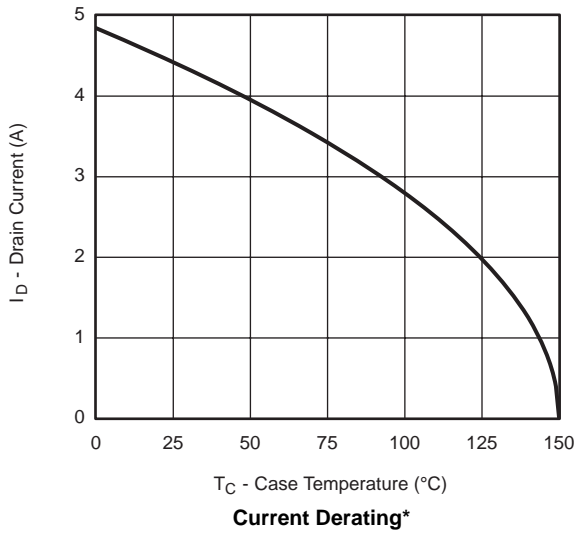
Single Pulse Power, Junction-to-Ambient



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

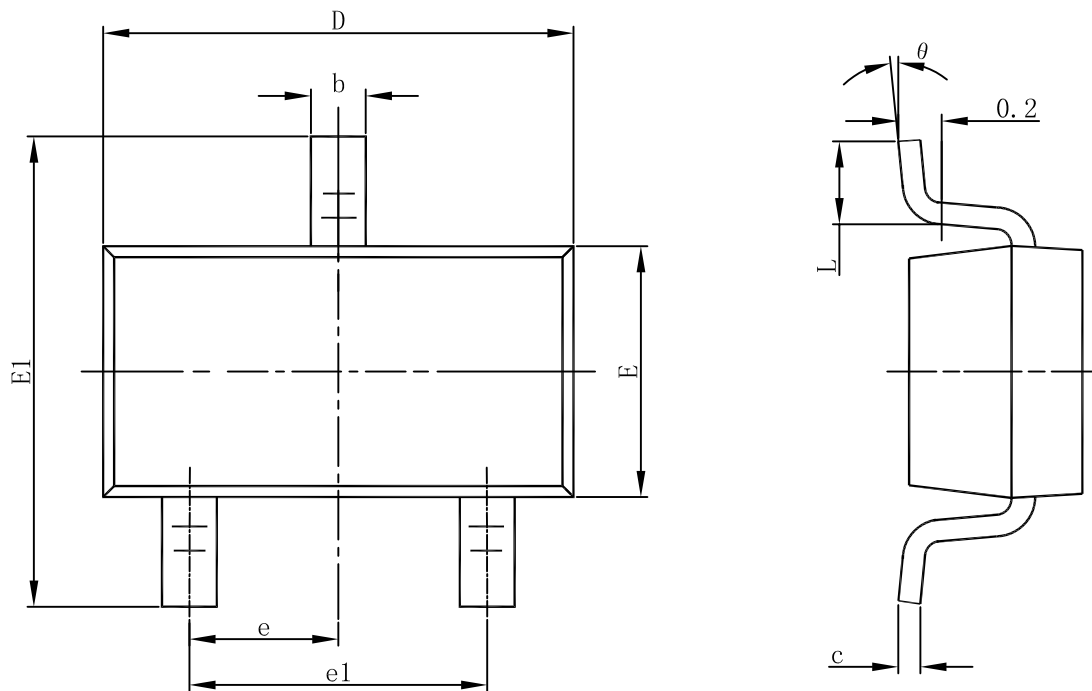
Safe Operating Area, Junction-to-Ambient

SCHOTTKY TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)

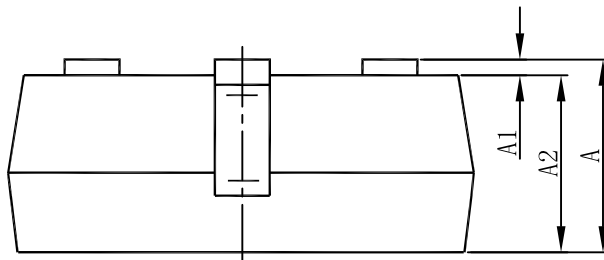


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

SOT23-3L Package Information



Top View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°